

Abstract of the Disclosure (Fig. 1):**THIN-FILM TRANSISTOR AND
METHOD FOR MANUFACTURING IT**

To achieve a large I_{ON}/I_{OFF} ratio of a thin-film transistor, an offset (ΔL) between the gate electrode (105) and source and drain regions (104, 103) is provided. This may be done by forming source and drain regions in a self-aligned manner by ion implantation using the gate electrode as a mask. Thereafter the gate electrode (105) is subjected to anodic oxidation at a voltage ranging from 150 to 250 V to obtain an offset (ΔL) of 100 to 200 μm .